Ordering number:EN5122A

DD54SC

Silicon Diffused Junction Type

Damper Diode for Ultrahigh-Definition Display Applications

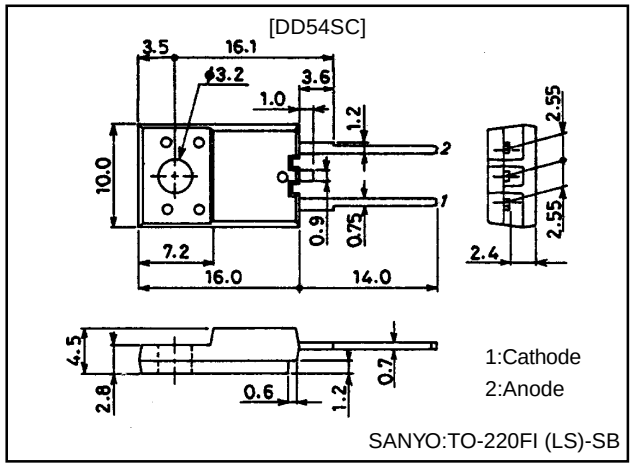
Features

- High breakdown voltage (V_{RRM}:1600V).
- High reliability.
- One-point fixing type plastic molded package facilitating easy mounting and heat dissipation.
- Fast forward/reverse recovery time.

Package Dimensions

unit:mm

1253A



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		1600	V
Non-repetitive Peak Reverse Voltage	V_{RSM}		1600	V
Average Output Current	I_O		5	A
Peak Output Current	Iop	PW≤100μs, duty≤50%	20	A
Surge Forward Current	I_{FSM}	Sine wave, 10ms	50	A
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Reverse Voltage	V_R	I_R=1mA	1600			V
Forward Voltage	V_F	I_F=5A			1.8	V
Reverse Current	I_R	V_R=1000V			200	μA
Reverse Recovery Time	t_{rr}	I_F=100mA, I_R=100mA			1.5	μs
Forward Recovery Time	t_{fr}	I_F=100mA		0.1	0.2	μs
Junction Capacitance	Cj	V_R=10V, f=100kHz		40		pF
Thermal Resistance	Rthj-c	Juntion-Case			3.75	˚C/W

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